

# Digital transistors (built-in resistors)

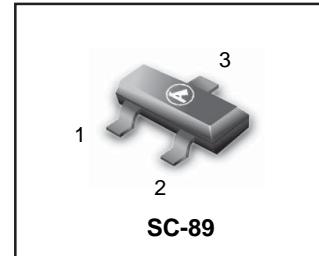
## ●Features

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making device design easy.

## ●Device marking

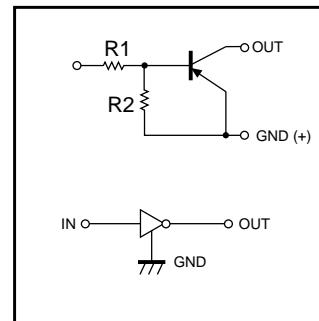
LDTA114EET1=6A

**LDTA114EET1**



## ●Absolute maximum ratings ( $T_a=25^{\circ}\text{C}$ )

| Parameter            | Symbol               | Value    | Unit |
|----------------------|----------------------|----------|------|
| Supply voltage       | $V_{cc}$             | -50      | V    |
| Input voltage        | $V_{IN}$             | -40~+10  | V    |
| Output current       | $I_o$                | -50      | mA   |
|                      | $I_{C(\text{Max.})}$ | -100     | mA   |
| Power dissipation    | $P_d$                | 150      | mW   |
| Junction temperature | $T_j$                | 150      | °C   |
| Storage temperature  | $T_{stg}$            | -55~+150 | °C   |



**●Electrical characteristics ( $T_a=25^\circ\text{C}$ )**

| Parameter            | Symbol              | Min. | Typ. | Max.  | Unit          | Conditions  |
|----------------------|---------------------|------|------|-------|---------------|---|
| Input voltage        | $V_{I(\text{off})}$ | —    | —    | -0.5  | V             | $V_{CC}=-5\text{V}$ , $I_o=100\mu\text{A}$                  |
|                      | $V_{I(\text{on})}$  | -3.0 | —    | —     |               | $V_o=-0.3\text{V}$ , $I_o=2\text{mA}$                       |
| Output voltage       | $V_{O(\text{on})}$  | —    | -0.1 | -0.3  | V             | $I_o/I_l=-10\text{mA}/-0.5\text{mA}$                        |
| Input current        | $I_I$               | —    | —    | -0.88 | mA            | $V_i=-5\text{V}$  |
| Output current       | $I_{O(\text{off})}$ | —    | —    | -0.5  | $\mu\text{A}$ | $V_{CC}=-50\text{V}$ , $V_i=0\text{V}$                      |
| DC current gain      | $G_I$               | 30   | —    | —     | —             | $V_o=-5\text{V}$ , $I_o=-5\text{mA}$                        |
| Input resistance     | $R_I$               | 7    | 10   | 13    | k $\Omega$    | —   |
| Resistance ratio     | $R_2/R_1$           | 0.8  | 1    | 1.2   | —             | —   |
| Transition frequency | $f_T$               | —    | 250  | —     | MHz           | $V_{CE}=-10\text{V}$ , $I_e=5\text{mA}$ , $f=100\text{MHz}$ |

\* Transition frequency of the device

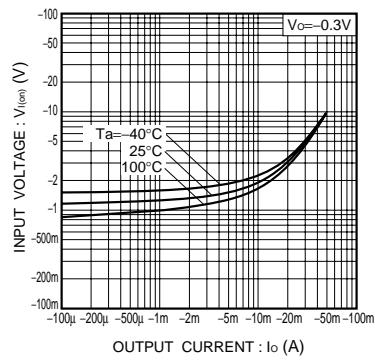
**●Electrical characteristic curves**


Fig.1 Input voltage vs. output current  
(ON characteristics)

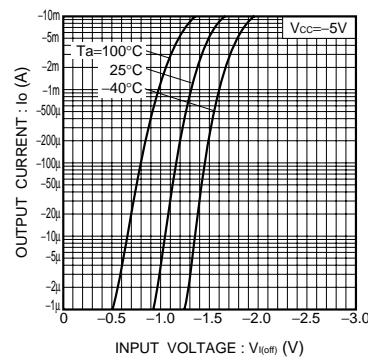


Fig.2 Output current vs. input voltage  
(OFF characteristics)

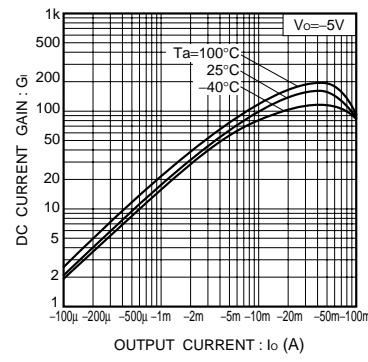


Fig.3 DC current gain vs. output current

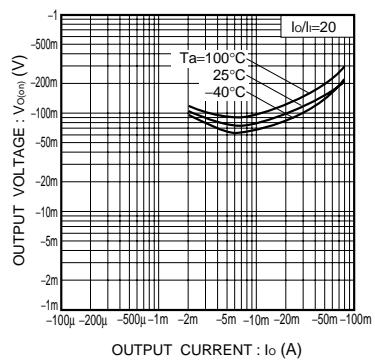
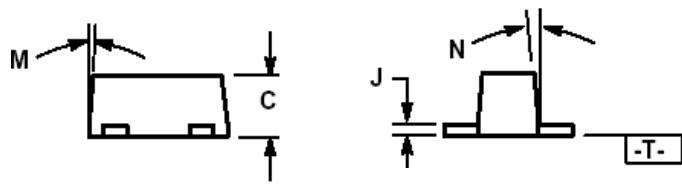
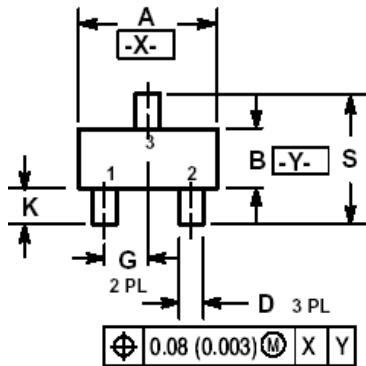


Fig.4 Output voltage vs. output current

**SC-89**


| DIM | MILLIMETERS |      |      | INCHES    |       |       |
|-----|-------------|------|------|-----------|-------|-------|
|     | MIN         | NOM  | MAX  | MIN       | NOM   | MAX   |
| A   | 1.50        | 1.60 | 1.70 | 0.059     | 0.063 | 0.067 |
| B   | 0.75        | 0.85 | 0.95 | 0.030     | 0.034 | 0.040 |
| C   | 0.60        | 0.70 | 0.80 | 0.024     | 0.028 | 0.031 |
| D   | 0.23        | 0.28 | 0.33 | 0.009     | 0.011 | 0.013 |
| G   | 0.50 BSC    |      |      | 0.020 BSC |       |       |
| H   | 0.53 REF    |      |      | 0.021 REF |       |       |
| J   | 0.10        | 0.15 | 0.20 | 0.004     | 0.006 | 0.008 |
| K   | 0.30        | 0.40 | 0.50 | 0.012     | 0.016 | 0.020 |
| L   | 1.10 REF    |      |      | 0.043 REF |       |       |
| M   | ---         | ---  | 10°  | ---       | ---   | 10°   |
| N   | ---         | ---  | 10°  | ---       | ---   | 10°   |
| S   | 1.50        | 1.60 | 1.70 | 0.059     | 0.063 | 0.067 |

